

In the Specification:

Please amend Paragraph 0016 as follows:

[0016] N-channel MOSFET 220 includes source and drain regions, 121 and 122. N-channel MOSFET [[120]] 220 also includes a gate 123 overlying a channel region 125. Channel region 125 is between source and drain regions, 121 and 122. Gate 123 and channel region 125 are separated from each other by a gate dielectric 124. In addition, ~~P-channel~~ N-channel MOSFET 220 includes an oxide region 228 within channel region 125. Oxide region 228 is laterally spaced from source and drain regions, 121 and 122. The region between oxide region 228 and gate 123 is preferably a strained channel. When a channel in N-channel MOSFET 220 is strained, hole mobilities in the strained channel generally are enhanced. Drive currents of N-channel MOSFET 220 are generally increased as well. Although it is currently believed that the strain imposed on the channel is the cause of the improved performance of the preferred embodiment devices, the scope of the present invention should not be limited to any particular mechanism or theory.